PRELIMINARY AMENDMENT

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Serial No. 10/808;059 Attorney Docket No. 400.285US01
Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE

LOW TEMPERATURE OXIDIZATION OF METALS

In the Claims

48. (currently amended) The method of claim 39 37 wherein the gate dielectric layer is formed on the substrate substantially between the source/drain regions.